## NSN 5962-01-444-6546

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View Online at https://aerobasegroup.com/nsn/5962-01-444-6546

Maximum Davier Discinction Batings
Maximum Power Dissipation Rating:
1.0 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
F-15i
Features Provided:
Electrostatic sensitive and monolithic and static operation
Inclosure Material:
Silicon
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Complementary-metal oxide-semiconductor logic
Criticality Code Justification:
Cbbl
Current Rating Per Characteristic:
15.00 milliamperes forward current, peak total value not applicable
Terminal Surface Treatment:
Solder
Product Name:
Microcircuit, memory, digital, cmos, 2k x 8 non-volatile static ram, monolithic silicon
Voltage Rating And Type Per Characteristic:
-0.6 volts total supply and 7.0 volts total supply
Time Rating Per Chacteristic:
55.00 nanoseconds access
Memory Device Type:
Ram
Special Features:
Descriptive designator cdip3-t28 or gdip4-t28; circuit function 8k x 8 nvsram
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
28 printed circuit
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:

No

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